

Claim 1 (amended). In an integrated semiconductor structure having a first layer, a second layer, and an intermediate layer, a contact structure extending through the first layer, the second layer, and the intermediate layer for electrically connecting regions of the semiconductor structure, the contact structure comprising:

a first contact hole filling in the first layer, a second contact hole filling in the second layer, and an intermediate structure in the intermediate layer disposed between the first layer and the second layer and connecting said first contact hole filling with said second contact hole filling, said intermediate structure forming an interconnect having a length between longitudinal ends thereof and a given width, and a contact area at each of said longitudinal ends with a contact area width greater than said given width.

Claim 2 (amended). The contact structure according to claim 1, wherein said interconnect is configured to connect two nearest points of a periodic basic grid disposed on said interconnect, to one another.

Enter The Following New Claims:

-- 10. The contact structure according to claim 1, wherein said first contact hole filling and said second contact hole

filling are the only contact hole fillings contacting said intermediate structure.

## BEST AVAILABLE COPY

11. In a DRAM having a first layer, a second layer, and an intermediate layer, a contact structure extending through the first layer, the second layer, and the intermediate layer for electrically connecting regions of the DRAM, the contact structure comprising:

a first contact hole filling in the first layer, a second contact hole filling in the second layer, and an intermediate structure in the intermediate layer disposed between the first layer and the second layer and connecting said first contact hole filling with said second contact hole filling, said intermediate structure forming an interconnect having a length between longitudinal ends thereof and a given width, and a contact area at each of said longitudinal ends with a contact area width greater than said given width.

12. The contact structure according to claim 11, wherein said interconnect is configured to connect two nearest points of a periodic basic grid disposed on said interconnect, to one another.

*A2*  
*ant*  
13. The contact structure according to claim 12, wherein said contact area of said intermediate structure is a square contact area at each end of the interconnect.

*Sub*  
*B1*  
14. The contact structure according to claim 13, wherein the contact areas and the interconnect define a bone-shape form of said intermediate structure.

15. The contact structure according to claim 11, wherein said intermediate layer is a metallization plane, and said intermediate structure is formed of a conductive material of the metallization plane.

16. The contact structure according to claim 11, wherein said contact hole fillings contain tungsten.

17. The contact structure according to claim 11, wherein the first and second layers are oxide layers.

18. The contact structure according to claim 11, wherein said first contact hole filling and said second contact hole filling are the only contact hole fillings contacting said intermediate structure. --

---